IS61NW6432



64K x 32 SYNCHRONOUS STATIC RAM WITH NO-WAIT STATE BUS FEATURE

FEATURES

- Fast access time:
 - 5 ns-100 MHz; 6 ns-83 MHz;
 - 7 ns-75 MHz; 8ns-66 MHz;
- · No wait cycles between Read and write
- · Internal self-timed write cycle
- Individual byte write Control
- Clock controlled, registered address, data and control
- Pentium[™] or Inear burst sequence control using MODE input
- Three chip enables for simple depth depth expansion and adress pipelining
- · Common data inputs and data outputs
- JEDEC 100-pin LQFP and PQFP package
- Single+3.3V power supply
- Optional data strobe pin (#80) for latching data (See page 12 for detailed timing)

DESCRIPTION

The IS61NW6432 is a high-speed, low-power synchronous static RAM designed to provide a burstable, high-performance, no-wait bus, secondary cache for the Pentium, 680X0, and Power PC microprocessors. It is organized as 65,536 words by 32 bits, fabricated with ICSI's advanced CMOS technology.

Incorporating a no-wait bus, wait cycles are eliminated when the bus switches from read to write, or write to read. This device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit.

All synchronous inputs pass through registers controlled by a Positive-edge-trggered clock input. Operations may be suspended and all synchronous inputs ignored when Clock Enable, $\overline{\text{CEN}}$ is HIGH. In this state the internal device will hold their previous values.

When the ADV/ $\overline{\text{LD}}$ is HIGH the internal burst counter is incremented. New external addresses can be loaded when ADV/ $\overline{\text{LD}}$ is LOW.

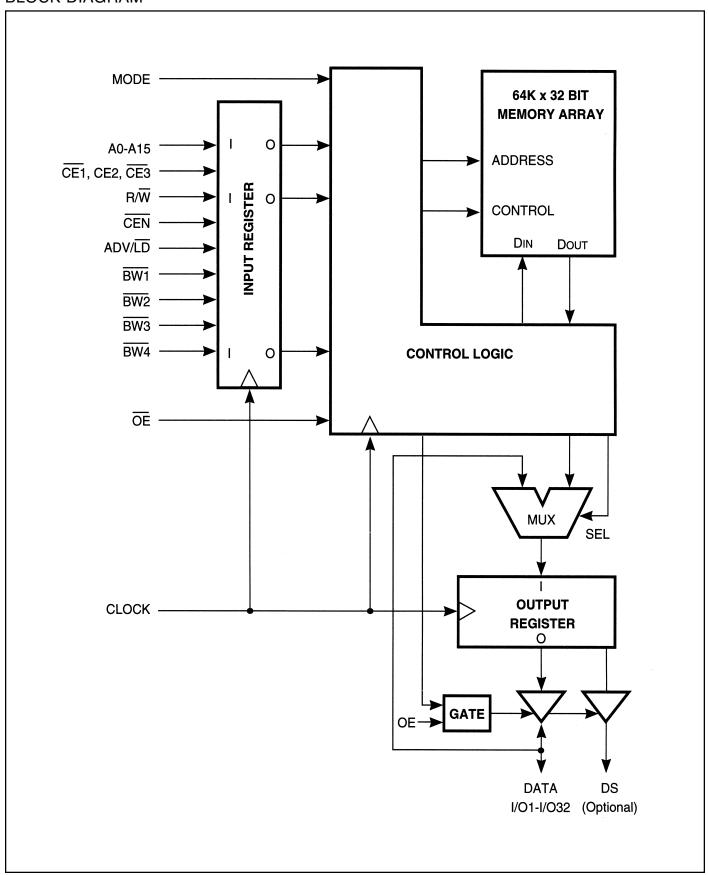
Write cycles are internally self-timed and are initiated by the rising edge of the clock inputs and when RD/ \overline{WE} is LOW. Separate byte enables allow indiviual bytes to be written. $\overline{BW1}$ controls I/O1-I/P8; $\overline{BW2}$ controls I/O9-I/O16; $\overline{BW3}$ controls I/O17-I/O24; $\overline{BW4}$ controls I/O25-I/O32. All Bytes are written when $\overline{BW1}$, $\overline{BW2}$, $\overline{BW3}$, and $\overline{BW4}$ are LOW.

MODE pin upon power up is in interleave burst mode. It can be connected to GND or Vccq to alter power up state.

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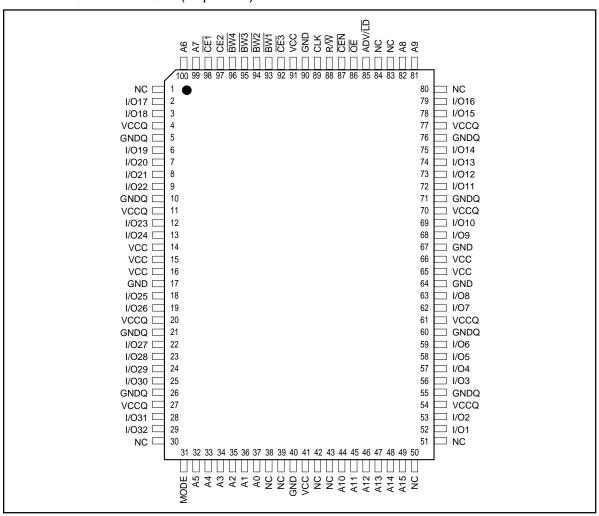


BLOCK DIAGRAM





PIN CONFIGURATION 100-Pin LQFP and PQFP (Top View)



PIN DESCRIPTIONS

A0-A15	Address Inputs
CLK	Clock
CEN	Clock Enale
ADV/CD	Advance Load
BW1-BW4	Synchronous Byte Write Enable
R/W	Read / Write
CE1, CE2, CE3	Synchronous Chip Enable
ŌĒ	Output Enable
DS ⁽¹⁾	Data Strobe

I/O-I/O32	Data Input/Output
MODE	Burst Sequence Mode
Vcc	+3.3V Power Supply
GND	Ground
Vccq	Isolated Output Buffer Supply: +3.3V
GNDa	Isolated Output Buffer Ground
NC	No Connect

Notes

^{1.} Optional, NC or DS.



TRUTH TABLE(1)

Operation	Address Used	R /₩	CEx	ADV/ LD	CEN	BW x	CLK
Bein New Write Cycle	External	L	L	L	L	Valid	L-H
Begin New Read Cycle	External	Н	L	L	L	Х	L-H
Advance Burst Counter(2)	Internal	Х	Х	Н	L	Valid	L-H
(Burst Write)							
Advance Burst Counter	Internal	Х	Х	Н	L	Х	L-H
(BurstRead)							
Deselect (2 Cycle)	Х	Х	Н	L	L	Х	L-H
Hold/NOOP ⁽⁴⁾	Х	Χ	Χ	Х	Н	Χ	L-H

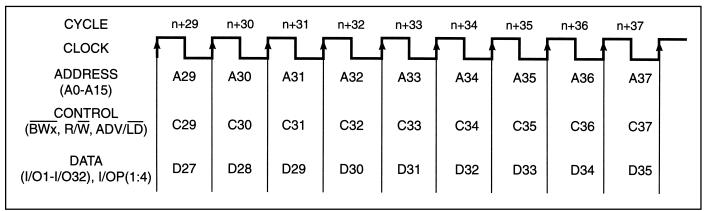
Notes:

- 1. "X" Means don't care.
- 2. When ADV/\(\overline{LD}\) signal is sampled HIIGH, the internal burst counter is incremented. The R/\(\overline{W}\) signal is ignored when the counter is advanced, Therefore, the nature of the burst cycle (Read or Write) is determined by the status of the R/\(\overline{W}\) signal when the first address is loaded at the beginning of the burst cycle.
- 3. Deselect cycle is initiated when \overline{CEx} is sampled HIGH and ADV/ \overline{LD} sampled LOW at rising edge of clock. The data bus will tristate two cycles after deselect is initiated.
- 4. When $\overline{\text{CEN}}$ is sampled high at the rising edge of clock, that clock edge is blocked form propagating through the part. The state of all the internal registers remains unchanged.

PARTIAL TRUTH TABLE(Non-burst)

Function	Ġ₩	BW1	BW2	BW3	BW4	CEx	ADV/ LD
READ	Н	Χ	Х	Χ	Χ	L	L
WRITE Byte 1	L	L	Н	Н	Н	L	L
WRITE Byte 2	L	Н	L	Н	Н	L	L
WRITE Byte 3	L	Н	Н	L	Н	L	L
WRITE Byte 4	L	Н	Н	Н	L	L	L
WRITE All Bytes	L	L	L	L	L	Χ	L

FUNCTIONAL TIMING DIAGRAM





TYPICAL OPERATION $\overline{\text{CE1}}$, $\overline{\text{CE3}}$ and $\overline{\text{CEN}}$ are LOW, CE2 is HIGH, Non-Burst Operation

Cycle	Address	R/W	ADV/LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	Н	L	L	L	Х	?	D-2	?
n+1	A1	L	L	L	L	L	?	D-1	?
n+2	A2	Н	L	L	L	Х	L	D0	Data Out
n+3	A3	L	L	L	L	L	Χ	D1	Data In
n+4	A4	Н	L	L	L	Χ	L	D2	Data Out
n+5	A 5	L	L	L	L	L	Χ	D3	Data In
n+6	A6	Н	L	L	L	Χ	L	D4	Data Out
n+7	A7	L	L	L	L	L	Χ	D5	Data In
n+8	A8	Н	L	L	L	Х	L	D6	Data Out
n+9	A9	L	L	L	L	L	Χ	D7	Data In
n+10	A10	Н	L	L	L	Χ	L	D8	Data Out
n+11	A11	Н	L	L	L	Χ	Χ	D9	Data In
n+12	A12	L	L	L	L	L	L	D10	Data Out
n+13	A13	L	L	L	L	L	L	D11	Data Out
n+14	A14	Н	L	L	L	Χ	Χ	D12	Data In
n+15	A15	Н	L	L	L	Χ	Χ	D13	Data In
n+16	A16	Н	L	L	L	Χ	L	D14	Data Out
n+17	A17	L	L	L	L	L	L	D15	Data Out
n+18	A18	L	L	L	L	L	L	D16	Data Out
n+19	A19	L	L	L	L	L	Х	D17	Data In
n+20	A20	Н	L	L	L	Х	Х	D18	Data In
n+21	A21	Н	L	L	L	Χ	Χ	D19	Data In

Notes

^{1.} H=High; L=Low; X=Don't Care;?=Don't Know; Z=High Impedance



READ OPERATION

Cycle	Address	R/W	ADV/ LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	Н	L	L	Х	Х	Χ	Χ	Address and Control meet setup
n+1	Х	Х	Х	L	L	Х	Х	Х	Clock Setup valid
n+2	Х	Х	Х	Х	Х	Х	L	D0	Contents of Address A0 Read Out

BURST READ OPERATION

Cycle	Address	R/W	ADV/ LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	Н	L	L	Х	Х	Х	Х	Address and Control meet setup
n+1	Х	Χ	Н	Χ	L	Х	Χ	Х	Clock Setup valid, Advance Counter
n+2	Х	Х	Н	Х	L	Х	L	D0	Address A0 Read Out, Inc. Count
n+3	Х	Х	Н	Х	L	Х	L	D0+1	Address A0+1 Read Out, Inc. Count
n+4	Х	Х	Н	Χ	L	Х	L	D0+2	Address A0+2 Read Out, Inc. Count
n+5	A1	Н	L	L	L	Х	L	D0+3	Address A0+3 Read Out, Load A1
n+6	Х	Х	Н	Х	L	Х	L	D0	Address A0 Read Out, Inc. Count
n+7	Х	Х	Н	Χ	L	Х	L	D1	Address A1 Read Out, Inc. Count
n+8	A2	Н	L	L	L	Х	L	D0+1	Address A0+1 Read Out, Load A2

WRITE OPERATION

Cycle	Address	R/W	ADV/ LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	L	L	L	L	L	Χ	Х	Address and Control meet setup
n+1	Х	Х	Х	L	L	Х	Х	Х	Clock Setup valid
n+2	Х	Х	Х	Х	L	Х	Х	D0	Write D0 to Address A0

BURST WRITE OPERATION

Cycle	Address	R/W	ADV/ LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	Н	L	L	L	L	Х	Х	Address and Control meet setup
n+1	Х	Х	Н	Х	L	L	Х	Х	Clock Setup valid, Inc. Count
n+2	Х	Х	Н	Х	L	L	Х	D0	Address A0 Write Out, Inc. Count
n+3	Х	Н	Н	L	L	Х	L	D0+1	Address A0+1 Write Out, Inc. Count
n+4	Х	Х	Н	Х	L	L	Х	D0+2	Address A0+2 Write Out, Inc. Count
n+5	A1	L	L	L	L	L	Χ	D0+3	Address A0+3 Write Out, Load A1
n+6	Х	Х	Н	Х	L	L	Х	D0	Address A0 Write Out, Inc. Count
n+7	Х	Х	Н	Х	L	L	Х	D1	Address A1 Write Out, Inc. Count
n+8	A2	L	L	L	L	L	Χ	D0+1	Address A0+1 Write Out, Load A2

Notes

1. H=High; L=Low; X=Don't Care;?=Don't Know; Z=High Impedance



READ OPERATION WITH CLOCK ENABLE USED

Cycle	Address	R/W	ADV/ LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	Н	L	L	L	Х	Х	Х	Address and Control meet setup
n+1	Х	Х	Х	Х	Н	Х	Х	Х	Clock n+1 Ignored
n+2	A1	Н	L	L	L	Х	Χ	Х	Clock Valid
n+3	Х	Х	Х	Х	Н	Х	L	D0	Clock Ignored, Data D0 is on the bus
n+4	Х	Х	Х	Х	Н	Х	L	D0	Clock Ignored, Data D0 is on the bus
n+5	A2	Н	L	L	L	Х	L	D0	Address A0 Read Out (bus trans.)
n+6	АЗ	?	L	L	L	Х	L	D1	Address A1 Read Out (bus trans.)
n+7	A4	?	L	L	L	Х	L	D2	Address A2 Read Out (bus trans.)

READ OPERATION WITH CLOCK ENABLE USED

Cycle	Address	R/W	ADV/ LD	CEX	CEN	BWX	ŌĒ	I/O	Comments
n	A0	L	L	L	L	L	Х	Х	Address and Control meet setup
n+1	Х	Х	Х	Х	Н	Х	Х	Х	Clock n+1 Ignored
n+2	A1	L	L	L	L	L	Х	Х	Clock Valid
n+3	Х	Х	Х	Χ	Н	Х	L	di	Clock Ignored.
n+4	Х	Χ	Х	Χ	Н	Х	L	di	Clock Ignored.
n+5	A2	L	L	L	L	L	L	D0	Write data D0 (bus trans.)
n+6	A3	?	L	L	L	L	L	D1	Write data D1 (bus trans.)
n+7	A4	?	L	L	L	L	L	D2	Write data D2 (bus trans.)

Notes

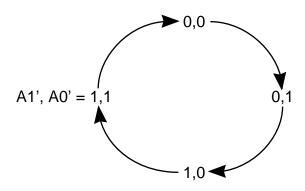
^{1.} H=High; L=Low; X=Don't Care;?=Don't Know; Z=High Impedance



INTERLEAVED BURST ADDRESS TABLE (MODE=Vccq or No connect)

External Address	1st Burst Address	2nd Burst Address	3rd Burst Addres	
A1 A0	A1 A0	A1 A0	A1 A0	
00	01	10	11	
01	00	11	10	
10	11	00	01	
11	10	01	00	

LINEAR BURST ADDRESS TABLE (MODE=GNDQ)



ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
TBIAS	Temperature Under Bias	-10 to +85	°C
Тѕтс	Storage Temperature	-55 to +150	°C
PD	Power Dissipation	1.8	W
Іоит	Output Current (per I/O)	100	mA
VIN, VOUT	Voltage Relative to GND for I/O Pins	-0.5 to Vccq + 0.3	V
Vin	Voltage Relative to GND for for Address and Control Inputs	-0.5 to 5.5	V

Notes:

- Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. This device contains circuity to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
- 3. This device contains circuitry that will ensure the output devices are in High-Z at power up.



OPERATING RANGE

Range	Ambient Temperature	Vcc
Commercial	0°C to +70°C	3.3V +10%, -5%

DC ELECTRICAL CHARACTERISTICS(1) (Over Operating Range)

Symbol	Parameter	Test Conditions		Min.	Max.	Unit
Vон	Output HIGH Voltage	lон = −5.0 mA		2.4	_	V
Vol	Output LOW Voltage	loL = 5.0 mA		_	0.4	V
VIH	Input HIGH Voltage			1.7	Vccq + 0.3	V
VIL	Input LOW Voltage			-0.3	0.8	V
lu	Input Leakage Current	$GND \leq Vin \leq Vccq^{(2)}$	Com.	– 5	5	μΑ
llo	Output Leakage Current	$GND \le V_{OUT} \le V_{CCQ}, \overline{OE} = V_{IH}$	Com.	– 5	5	μΑ

POWER SUPPLY CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	-5 Min.Typ. Max.	-6 Min.Typ.Max.	-7 Min.Typ.Max.	-8 Min.Typ.Max.	Unit
Icc	AC Operating Supply Current	Device Selected, Com. All Inputs = V_{\parallel} or V_{\parallel} H \overline{OE} = V_{\parallel} H,Cycle Time \geq txc min	— — 230 I.	220	210	200	mA
Isb	Standby Current	Device Deselected, Com. Vcc = Max., All Inputs= V _{IH} or V _{IL} CLK Cycle Time ≥ tκc min. CEN=V _{IH}	60	60	60	60	mA

Note:

^{1.} MODE pin has an internal pull up. This pin may be a No Connect, tied to GND, or tied to Vccq.

^{2.} MODE pin should be tied to Vcc or GND. It exhibit $\pm 30~\mu$ A maximum leakage current when tied to \leq GND + 0.2V or \geq Vcc - 0. 2V.



CAPACITANCE(1,2)

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	6	pF
Соит	Input/Output Capacitance	Vout = 0V	8	pF

Notes:

- Tested initially and after any design or process changes that may affect these parameters.
 Test conditions: T_A = 25°C, f = 1 MHz, Vcc = 3.3V.

AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1

AC TEST LOADS

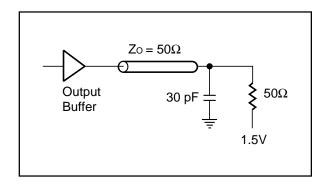


Figure 1

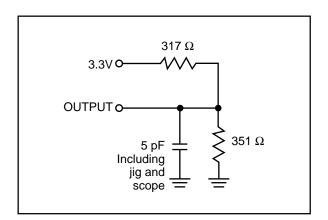


Figure 2



READ /WRITE CYCLE SWITCHING CHARACTERISTICS (Over Operating Range)

			-5	-(-		-7	-8		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Unit
fmax	Clock Frequency	_	100	_	83	_	75	_	66	MHz
tĸc	Cycle Time	10	_	12	_	13	_	15	_	ns
tкн	Clock High Time	4	_	4	_	6	-	6	-	ns
tkl	Clock Low Time	4	_	4	_	6	_	6	_	ns
tka	Clock Access Time	_	5	_	6	_	7	_	8	ns
tkqx ⁽²⁾	Clock High to Output Invalid	1.5	_	1.5	_	1.5	_	1.5	_	ns
tkqlz ⁽²⁾	Clock High to Output Low-Z	2.0	_	2.0	_	2.0	_	2.0	_	ns
tkqhz ⁽²⁾	Clock High to Output High-Z	1.5	3.5	2	3.5	2	3.5	2	3.5	ns
toeq	Output Enable to Output Valid	_	5	_	6	_	6	_	6	ns
toeqx(2)	Output Disable to Output Invalid	0	_	0	_	0	_	0	_	ns
toelz(2)	Output Enable to Output Low-Z	0	_	0	_	0	_	0	_	ns
toehz(2)	Output Disable to Output High-Z	_	3.5	_	3.5	_	3.5	_	3.5	ns
tas	Address Setup Time	2.0	_	2.0	_	2.0	_	2.0	_	ns
tws	Read/Write Setup Time	2.0	_	2.0	_	2.0	_	2.0	_	ns
tces	Chip Enable Setup Time	2.0	_	2.0	_	2.0	_	2.0	_	ns
tse	Clock Enable Setup Time	2.0	_	2.0	_	2.0	_	2.0	_	ns
tavs	Address Advance Setup Time	2.0	_	2.0	_	2.0	_	2.0	_	ns
tae	Address Hold Time	0.5	_	0.5	_	0.5	_	0.5	_	ns
the	Clock EnableHold Time	0.5	_	0.5	_	0.5	_	0.5	_	ns
twн	Write Hold Time	0.5	_	0.5	_	0.5	_	0.5	_	ns
tceh	Chip Enable Hold Time	0.5	_	0.5	_	0.5	_	0.5	_	ns
tals	Advance/Load (ADV/LD) Setup Tii	me2.0	_	2.0	_	2.0	_	2.0	_	ns
talh	Advance/Load (ADV/LD) Hold Tin	ne 0.5	_	0.5	_	0.5	_	0.5	_	ns
tds	Data Setup Time	2.0	_	2.0	_	2.0	_	2.0	_	ns
tdh	Data Hold Time	0.5	_	0.5	_	0.5	_	0.5	_	ns
tzp	I/O From Tri-State to Valid	1.5	_	1.5	2.5	1.5	2.5	1.5	2.5	ns

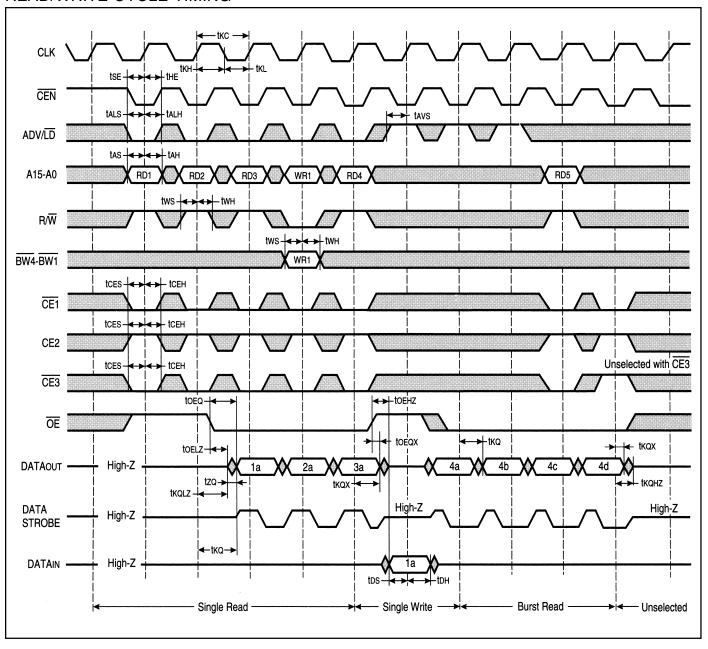
Notes:

^{1.} Configuration signal MODE is static and must not change during normal operation.

^{2.} Guaranteed but not 100% tested. This parameter is periodically sampled.



READ/WRITE CYCLE TIMING





ORDERING INFORMATION

Commercial Range: 0°C to +70°C

Frequency (MHz)	Order Part Number	Package
5		14*20*1.4mm LQFP 14*20*2.7mm PQFP
6		14*20*1.4mm LQFP 14*20*2.7mm PQFP
7		14*20*1.4mm LQFP 14*20*2.7mm PQFP
8		14*20*1.4mm LQFP 14*20*2.7mm PQFP



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